

ABSTRACT OF THE DISCLOSURE

A conductive material such as silver is charged in a via hole of an insulative substrate made of low-temperature-sintered ceramic. A lower electrode, a dielectric layer, and an upper electrode are formed in a thin film on the insulative substrate. Thus a thin-film capacitor element is formed in which the capacitance value of the capacitor is specified by the overlapping part of the lower electrode and the upper electrode opposed through the dielectric layer. The dielectric layer is shaped like a ring with the via hole (conductive material) as the center and the part exposed inward from the inner periphery of the dielectric layer is served as a lead section of the lower electrode. The lead section is connected to a ground electrode on the back of the insulative substrate through the conductive material.